



DMT3020LFDBQ

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max T _A = +25°C
2014	20mΩ @ V _{GS} = 10V	7.7A
30V	32mΩ @ V _{GS} = 4.5V	6.1A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- General Purpose Interfacing Switch
- Power Management Functions

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

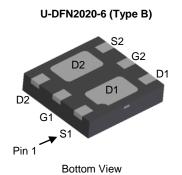
Features and Benefits

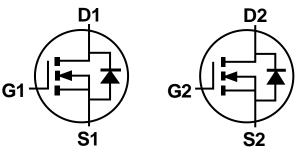
- 0.6mm Profile Ideal for Low Profile Applications
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMT3020LFDBQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)





Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3020LFDBQ-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMT3020LFDBQ-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Site 1:

U-DFN2020-6 (Type B)



Y2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020)M = Month (ex: 9 = September)

Date Code Key												
Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н		J	K	L	М	Ν	0	Р	R	S	Т
Month	lan	Feb	Mar	Apr	May	lun	Jul	Aug	Sep	Oct	Nov	Dec
wonth	Jan	гер	IVIAI	Apr	Iviay	Jun	Jui	Aug	öcp	00	107	
Code	1	2	3	4	5	6	7	8	9	0	Ν	D

Site 2:

U-DFN2020-6 (Type B)

Y2 = Product Type Marking Code YWX = Date Code Marking

 $Y = Y ear (ex: 0 = 2020) \\ W = Week (ex: a = week 27; z Represents Week 52 and 53) \\ X = Internal Code (ex: U = Monday)$

Date Code Key													
Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	
Code	0	1	2	3	4	5	6	7	8	9	0	1	
Week		1	-26			27-52			53				
Code		A	λ-Ζ			a-z					Z		
Internal Code	Su	ın	Mor	n	Tue	Tue Wed Thu			1	Fri		Sat	
Code	٦		U		V		W	Х		Y		Z	



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
	+25°C I _D +75°C	7.7 6.2	А
Maximum Continuous Body Diode Forward Current (Note 6)	ls	2	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	IDM	50	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	170	°C/W
Total Power Dissipation (Note 6)		PD	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	70	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

				_				
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)		BV _{DSS}			r		I	
Drain-Source Breakdown Voltage	5		30	_	—	V	$V_{GS} = 0V, I_D = 250\mu A$	
	T _J = +25°C	IDSS	—	—	1	μA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage		lgss	—		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage		VGS(TH)	1.0	-	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance		Deserve			20	mΩ	VGS = 10V, ID = 9.0A	
Static Dialit-Source Off-Resistance		RDS(ON)	_	_	32	11152	$V_{GS} = 4.5V, I_D = 7.0A$	
Diode Forward Voltage		Vsd	_	_	1.0	V	$V_{GS} = 0V$, $I_S = 2A$	
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance		Ciss		393	—	pF		
Output Capacitance		Coss	—	173	—	pF	V _{DS} = 15V, V _{GS} = 0V, - f = 1.0MHz	
Reverse Transfer Capacitance		Crss	_	27	—	pF		
Gate Resistance		Rg	_	1.1	—	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)		Qg	_	7.0	—	nC		
Total Gate Charge (V _{GS} = 4.5V)		Qg	_	3.6	—	nC		
Gate-Source Charge		Qgs		0.9	_	nC	$V_{DD} = 15V, I_D = 9A$	
Gate-Drain Charge		Qgd		1.5	_	nC	7	
Turn-On Delay Time		td(on)		1.8	_	ns		
Turn-On Rise Time		t _R		1.9	_	ns	V _{DD} = 15V, V _{GS} = 10V,	
Turn-Off Delay Time		tD(OFF)		7.5	_	ns	$R_G = 6\Omega, I_D = 9A$	
Turn-Off Fall Time	Turn-Off Fall Time			2.4	—	ns		
Reverse Recovery Time		t _{RR}	—	10	—	ns		
Reverse Recovery Charge		Qrr		2.6	—	nC	IF = 9A, di/dt = 100A/µs	

 Notes:
 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

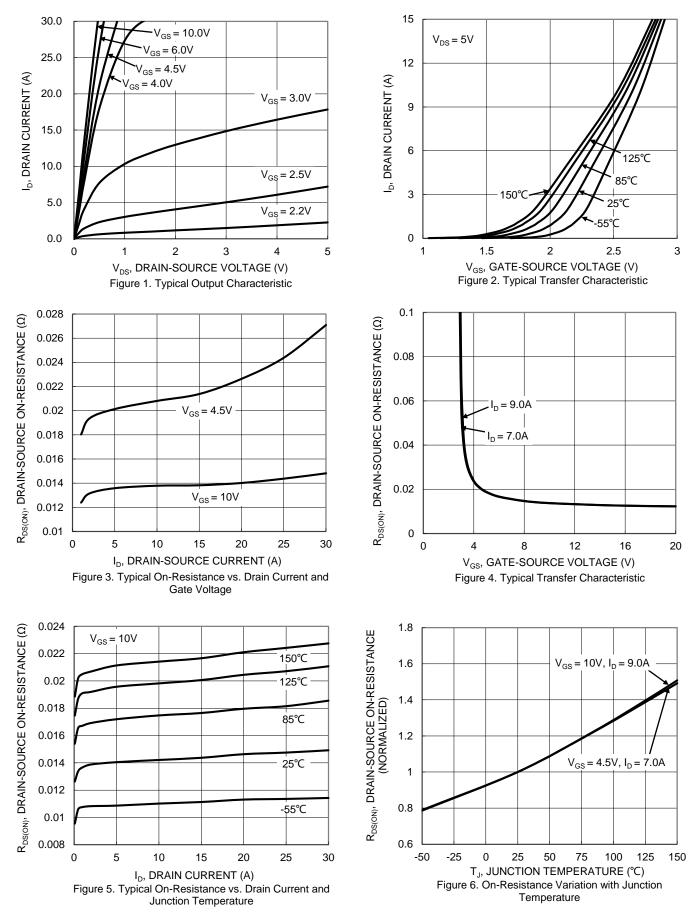
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

 7. Short duration pulse test used to minimize self-heating effect.

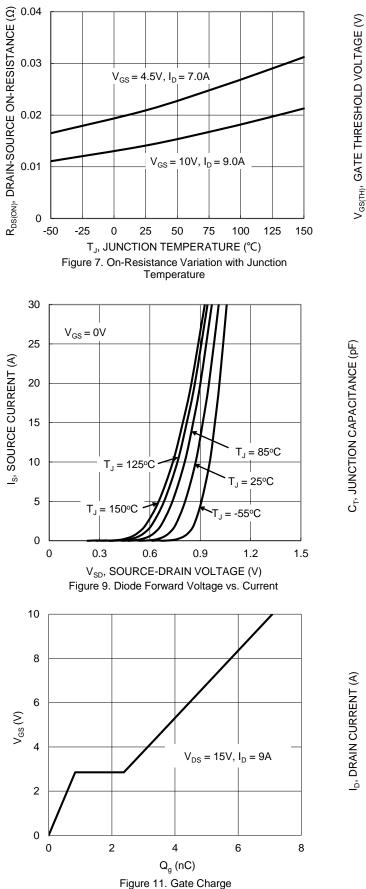
 8. Guaranteed by design. Not subject to product testing.

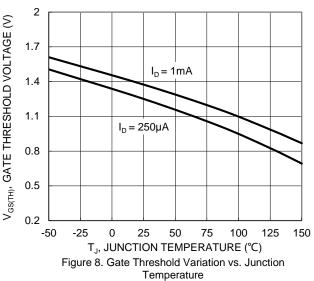


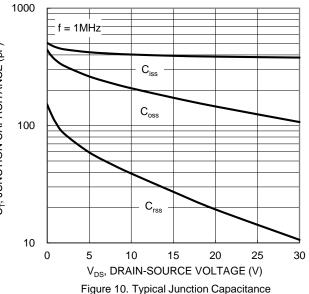
DMT3020LFDBQ

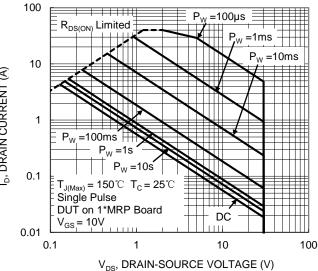


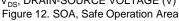




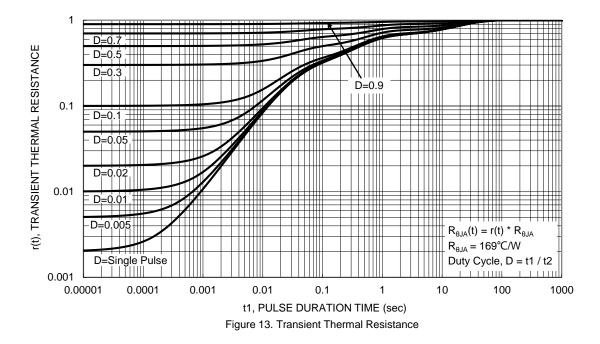








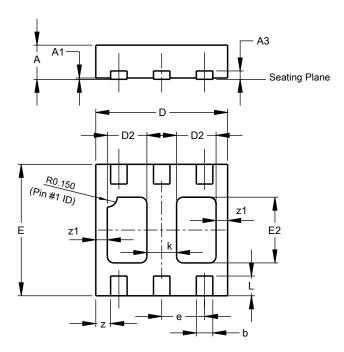






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



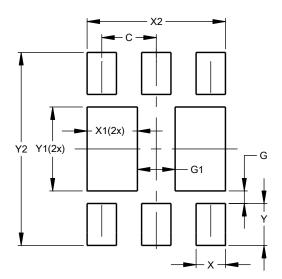
	U-DFN2020-6								
Dim	Type B m Min Max Typ								
Α	0.545	0.605	0.575						
A1	0.00	0.05	0.02						
A3	-	-	0.13						
b	0.20	0.30	0.25						
D	1.95	2.075	2.00						
D2	0.50	0.70	0.60						
е	-	-	0.65						
Е	1.95	2.075	2.00						
E2	0.90	1.10	1.00						
k	-	-	0.45						
L	0.25	0.35	0.30						
z	-	-	0.225						
z1	-	-	0.175						
All	Dimens	ions in	mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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